

CdS
 0,143 - . -
 CdS
 0,3 . 2,423 , CdS
 - 2,427 .
 CdS 550-850 (80-95) %.
 " " -
 CdS/CdTe.
 CdS 0,3 .

: 1. Martinez M.A., Herrero J., Gutierrez M.T. Properties of RF sputtered zinc oxide based thin films made from different targets // Solar Energy Materials and Solar Cells. -1994. - P. 489-498.

: 539.216:546.28'26

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-

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[1,2]

SiC

-

(1200°) .

(~8%)

,

SiC.

-

[1]

SiC

(~800°). [1]

: 1.

-2003.- . 10.- . 113-120. 2. Mehregany M., Zorman C.A., Roy S. Silicon carbide for microelectromechanical systems // International Materials Reviews.-2000.-V.45.- 3.- .85-105.

621.47:578.12

CdTe

()

(. [1]).

CdS/CdTe.

16,5 %,

[2].

CdS/CdTe,